2SK1862, 2SK1863

Silicon N-Channel MOS FET

HITACHI

ADE-208-1329 (Z) 1st. Edition Mar. 2001

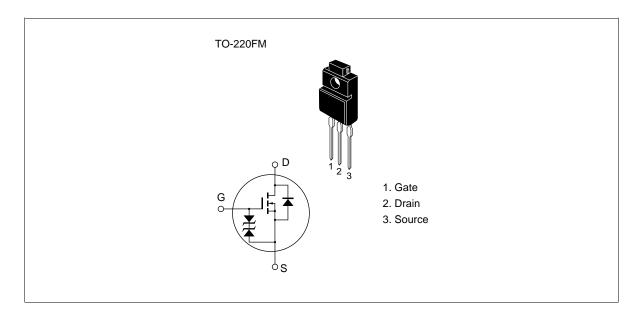
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for Switching regulator

Outline





2SK1862, 2SK1863

Absolute Maximum Ratings (Ta = 25°C)

Item		Symbol	Ratings	Unit
Drain to source voltage	2SK1862	$V_{\scriptscriptstyle DSS}$	450	V
	2SK1863	V _{DSS}	500	
Gate to source voltage		V _{GSS}	±30	V
Drain current		I _D	3	A
Drain peak current		l _{D(pulse)} *1	12	A
Body to drain diode reverse drain current		I _{DR}	3	A
Channel dissipation		Pch*2	25	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-55 to +150	°C

Notes 1. PW \leq 10 μ s, duty cycle \leq 1 %

^{2.} Value at Tc = 25 °C

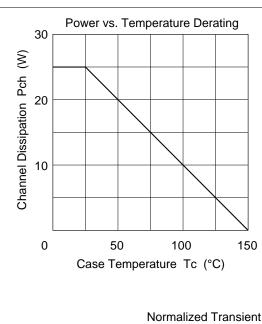
Electrical Characteristics ($Ta = 25^{\circ}C$)

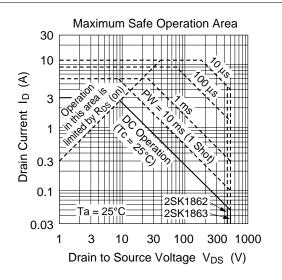
Item		Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source	2SK1862	$V_{(BR)DSS}$	450	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
breakdown voltage	2SK1863		500				
Gate to source b voltage	reakdown	$V_{(BR)GSS}$	±30	_	_	V	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source le	eak current	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate	2SK1862	I _{DSS}	_	_	250	μΑ	$V_{DS} = 360 \text{ V}, V_{GS} = 0$
voltage drain current	2SK1863	_					$V_{DS} = 400 \text{ V}, V_{GS} = 0$
Gate to source co	utoff voltage	$V_{GS(off)}$	2.0	_	3.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to	2SK1862	R _{DS(on)}	_	2.0	2.8	Ω	$I_D = 2 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$
source on state resistance	2SK1863		_	2.2	3.0		
Forward transfer	admittance	y _{fs}	1.5	2.5	_	S	I _D = 2 A V _{DS} = 10 V* ¹
Input capacitance	е	Ciss	_	330	_	pF	V _{DS} = 10 V
Output capacitan	ice	Coss	_	90	_	pF	$V_{GS} = 0$
Reverse transfer	capacitance	Crss	_	15	_	pF	f = 1 MHz
Turn-on delay tim	ne	t _{d(on)}	_	7	_	ns	I _D = 2 A
Rise time		t,	_	20	_	ns	V _{GS} = 10 V
Turn-off delay tim	ne	t _{d(off)}	_	30	_	ns	$R_L = 15 \Omega$
Fall time		t _f	_	20	_	ns	
Body to drain dio voltage	de forward	V_{DF}	_	0.9	_	V	$I_F = 3 \text{ A}, V_{GS} = 0$
Body to drain dio recovery time	de reverse	t _{rr}		300		ns	$I_F = 3 \text{ A}, V_{GS} = 0,$ $di_F / dt = 100 \text{ A} / \mu \text{s}$

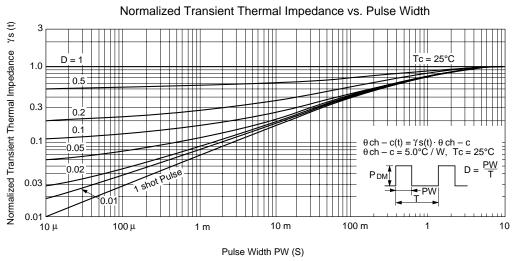
Note 1. Pulse Test

See characteristic curves of 2SK1153, 2SK1154

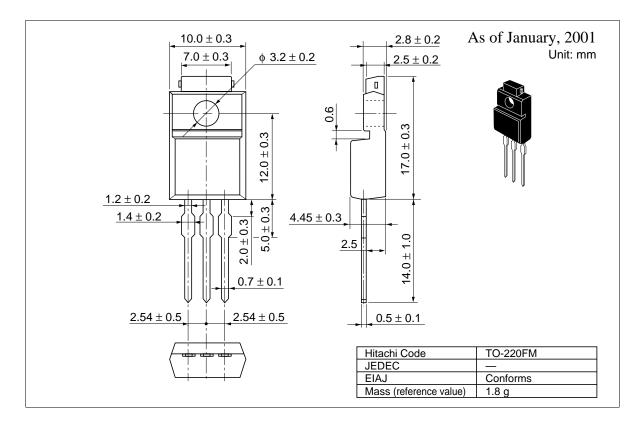
2SK1862, 2SK1863







Package Dimensions



Cautions

- 1. Hitachi neither warrants nor grants licenses of any rights of Hitachi's or any third party's patent, copyright, trademark, or other intellectual property rights for information contained in this document. Hitachi bears no responsibility for problems that may arise with third party's rights, including intellectual property rights, in connection with use of the information contained in this document.
- 2. Products and product specifications may be subject to change without notice. Confirm that you have received the latest product standards or specifications before final design, purchase or use.
- 3. Hitachi makes every attempt to ensure that its products are of high quality and reliability. However, contact Hitachi's sales office before using the product in an application that demands especially high quality and reliability or where its failure or malfunction may directly threaten human life or cause risk of bodily injury, such as aerospace, aeronautics, nuclear power, combustion control, transportation, traffic, safety equipment or medical equipment for life support.
- 4. Design your application so that the product is used within the ranges guaranteed by Hitachi particularly for maximum rating, operating supply voltage range, heat radiation characteristics, installation conditions and other characteristics. Hitachi bears no responsibility for failure or damage when used beyond the guaranteed ranges. Even within the guaranteed ranges, consider normally foreseeable failure rates or failure modes in semiconductor devices and employ systemic measures such as failsafes, so that the equipment incorporating Hitachi product does not cause bodily injury, fire or other consequential damage due to operation of the Hitachi product.
- 5. This product is not designed to be radiation resistant.
- 6. No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without written approval from Hitachi.
- 7. Contact Hitachi's sales office for any questions regarding this document or Hitachi semiconductor products.

IIΤΔ(;⊦

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL NorthAmerica : http://semiconductor.hitachi.com/ Europe http://www.hitachi-eu.com/hel/ecg Asia http://sicapac.hitachi-asia.com

Japan http://www.hitachi.co.jp/Sicd/indx.htm

For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose,CA 95134 Tel: <1> (408) 433-1990 Germany

Hitachi Europe GmbH Electronic Components Group Dornacher Straße 3 D-85622 Feldkirchen, Munich Fax: <1>(408) 433-0223 Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00

> Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <886>-(2)-2718-3666 Tel: <44> (1628) 585000 Fax: <44> (1628) 585160

Hitachi Asia Ltd. Hitachi Tower 16 Collyer Quay #20-00, Singapore 049318 Tel: <65>-538-6533/538-8577

Fax: <65>-538-6933/538-3877 URL: http://www.hitachi.com.sg

Hitachi Asia Ltd (Taipei Branch Office) 4/F, No. 167, Tun Hwa North Road, Hung-Kuo Building. Taipei (105), Taiwan

Fax: <886>-(2)-2718-8180 Telex: 23222 HAS-TP URL: http://www.hitachi.com.tw Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road Tsim Sha Tsui, Kowloon, Hong Kong

Tel: <852>-(2)-735-9218 Fax: <852>-(2)-730-0281 URL: http://www.hitachi.com.hk

Copyright © Hitachi, Ltd., 2000. All rights reserved. Printed in Japan. Colophon 2.0